## **SQ2301ES**

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**Vishay Siliconix** 

## Automotive P-Channel 20 V (D-S) 175 °C MOSFET



- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified d
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

GC

P-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-20			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.120			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 V$	0.180			
I <sub>D</sub> (A)	-3.9			
Configuration	Single			

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2301ES (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	-20	v	
Gate-source voltage		V <sub>GS</sub>	± 8	V	
Continuous drain current	T <sub>C</sub> = 25 °C		-3.9		
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-2.2		
Continuous source current (diode conduction)	I <sub>S</sub>	-3.7	A		
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	-15		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-9	-	
Single pulse avalanche energy	L = 0.1 MH	E <sub>AS</sub>	4	mJ	
	T <sub>C</sub> = 25 °C	D	3	w	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1	vv	
Operating junction and storage temperature range	)	T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	166	°C/W		
Junction-to-case (drain)		R <sub>thJF</sub>	50	0/10		

#### Notes

a. Package limited

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

c. When mounted on 1" square PCB (FR-4 material)

d. Parametric verification ongoing

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = -250 μA		-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-	-1.5	v
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	$V_{DS} = -20 \text{ V}, \text{ T}_{\text{J}} = 175 ^{\circ}\text{C}$	-	-	-150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -4.5 V$	$V_{DS} \ge 5 V$	-8	-	-	Α
	P	$V_{GS} = -4.5 V$	I <sub>D</sub> = -2.8 A	-	0.080	0.120	0
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -2 A	-	0.110	0.180	Ω
Forward transconductance <sup>a</sup>		V <sub>DS</sub> =	-1.6 V, I <sub>D</sub> = -2.8 A	-	7	-	S
Dynamic <sup>b</sup>	·						
Input capacitance	C <sub>iss</sub>			-	340	425	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -10 V, f = 1 MHz	-	80	100	
Reverse transfer capacitance	C <sub>rss</sub>			-	55	70	
Total gate charge <sup>c</sup>	Qg			-	5	8	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -2.8 \text{ A}$	-	0.7	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>				1.3	-	1
Gate resistance	Rg	f = 1 MHz		5.5	10	14.5	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	15	22	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -10 V, R <sub>L</sub> = 10 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω		-	14	21	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	30	45	
Fall time <sup>c</sup>	t <sub>f</sub>			-	9	15	
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-15	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -1.6 A, V <sub>GS</sub> = 0		-	-0.8	-1.2	V

Notes

e. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty~cycle} \leq 2~\%$ 

f. Guaranteed by design, not subject to production testing

g. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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T<sub>C</sub> = 25 °C

2

T<sub>C</sub> = 125 °C

3

 $V_{GS} = 2.5 V$ 

 $V_{GS} = 4.5 V$ 

6

I<sub>D</sub> - Drain Current (A)

**On-Resistance vs. Drain Current** 

 $V_{DS} = 10 V$ 

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 $\rm V_{GS}$  - Gate-to-Source Voltage (V)

**Transfer Characteristics** 

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55 °C

T<sub>C</sub>

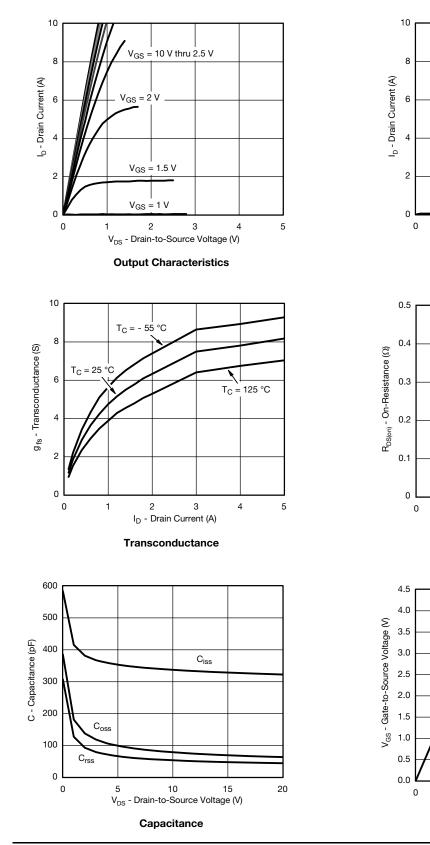
1

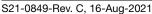
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I<sub>D</sub> = 2.8 A

4

## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)





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Q<sub>g</sub> - Total Gate Charge (nC) **Gate Charge** 

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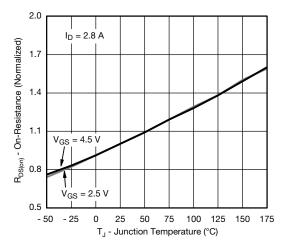
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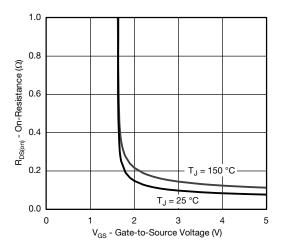
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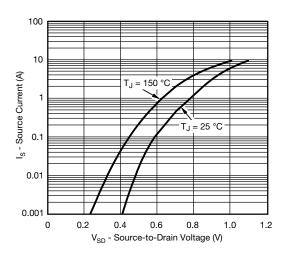
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



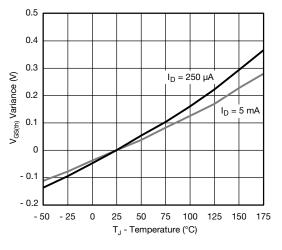
**On-Resistance vs. Junction Temperature** 



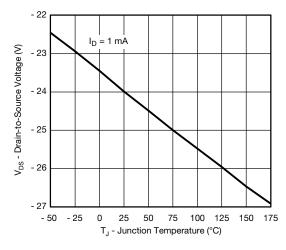
**On-Resistance vs. Gate-to-Source Voltage** 



Source-Drain Diode Forward Voltage





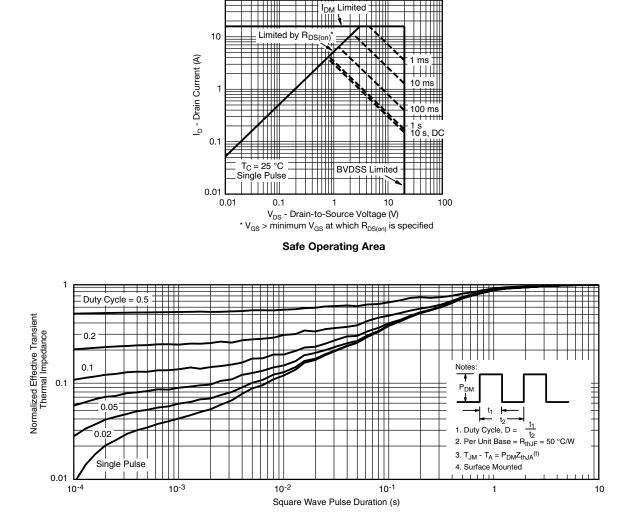


Drain Source Breakdown vs. Junction Temperature

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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

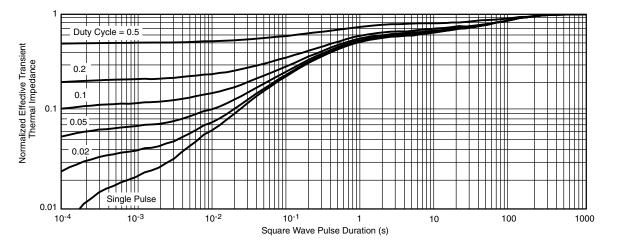


Normalized Thermal Transient Impedance, Junction-to-Foot

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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

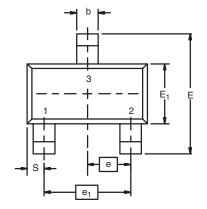
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?66718</u>.



# Package Information

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## SOT-23 (TO-236): 3-LEAD



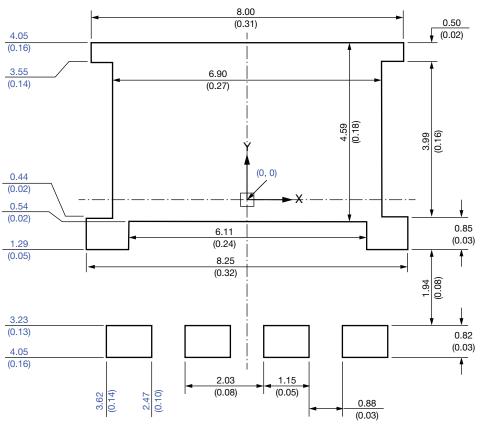




Dim	MILLIM	IETERS	INCHES		
	Min	Мах	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC 0.0748 Ref		8 Ref	
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64	0.64 Ref		5 Ref	
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



# **Recommended Minimum PADs for PowerPAK® 8 x 8L Single**



Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



# Application Note 826

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### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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